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Kind regards,

Team Nexperia
1. Product profile

1.1 General description
PNP low $V_{\text{CEsat}}$ Breakthrough In Small Signal (BISS) transistor in a SOT89 (SC-62/TO-243) SMD plastic package.

NPN complement: PBSS8110X.

1.2 Features

- SOT89 package
- Low collector-emitter saturation voltage $V_{\text{CEsat}}$
- High collector current capability $I_C$ and $I_{\text{CM}}$
- High efficiency leading to less heat generation

1.3 Applications

- Major application segments:
  - Automotive 42 V power
  - Telecom infrastructure
  - Industrial
- Peripheral driver:
  - Driver in low supply voltage applications (e.g. lamps and LEDs)
  - Inductive load driver (e.g. relays, buzzers and motors)
- DC-to-DC conversion

1.4 Quick reference data

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Parameter</th>
<th>Conditions</th>
<th>Min</th>
<th>Typ</th>
<th>Max</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>$V_{\text{CEO}}$</td>
<td>collector-emitter voltage</td>
<td>open base</td>
<td>-</td>
<td>-</td>
<td>$-100$</td>
<td>V</td>
</tr>
<tr>
<td>$I_C$</td>
<td>collector current (DC)</td>
<td>-</td>
<td>-</td>
<td>-1</td>
<td>A</td>
<td></td>
</tr>
<tr>
<td>$I_{\text{CM}}$</td>
<td>peak collector current</td>
<td>single pulse; $t_p \leq 1$ ms</td>
<td>-</td>
<td>-</td>
<td>$-3$</td>
<td>A</td>
</tr>
<tr>
<td>$R_{\text{CEsat}}$</td>
<td>collector-emitter saturation resistance</td>
<td>$I_C = -1$ A; $I_B = -100$ mA</td>
<td>[1]</td>
<td>170</td>
<td>320</td>
<td>mΩ</td>
</tr>
</tbody>
</table>

[1] Pulse test: $t_p \leq 300$ μs; $\delta \leq 0.02$. 

PBSS9110X
100 V, 1 A PNP low $V_{\text{CEsat}}$ (BISS) transistor
Rev. 02 — 22 November 2009 Product data sheet
2. Pinning information

Table 2. Pinning

<table>
<thead>
<tr>
<th>Pin</th>
<th>Description</th>
<th>Simplified outline</th>
<th>Symbol</th>
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<tbody>
<tr>
<td>1</td>
<td>emitter</td>
<td></td>
<td></td>
</tr>
<tr>
<td>2</td>
<td>collector</td>
<td></td>
<td></td>
</tr>
<tr>
<td>3</td>
<td>base</td>
<td></td>
<td></td>
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</table>

3. Ordering information

Table 3. Ordering information

<table>
<thead>
<tr>
<th>Type number</th>
<th>Package</th>
<th>Description</th>
<th>Version</th>
</tr>
</thead>
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<tr>
<td>PBSS9110X</td>
<td>SC-62</td>
<td>plastic surface mounted package; collector pad for good heat transfer; 3 leads</td>
<td>SOT89</td>
</tr>
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</table>

4. Marking

Table 4. Marking codes

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<th>Marking code[1]</th>
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<tr>
<td>PBSS9110X</td>
<td>*4C</td>
</tr>
</tbody>
</table>

[1] * = -: made in Hong Kong  
* = p: made in Hong Kong  
* = t: made in Malaysia  
* = W: made in China
5. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Parameter</th>
<th>Conditions</th>
<th>Min</th>
<th>Max</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>( V_{CBO} )</td>
<td>collector-base voltage</td>
<td>open emitter</td>
<td>-</td>
<td>-120</td>
<td>V</td>
</tr>
<tr>
<td>( V_{CEO} )</td>
<td>collector-emitter voltage</td>
<td>open base</td>
<td>-</td>
<td>-100</td>
<td>V</td>
</tr>
<tr>
<td>( V_{EBO} )</td>
<td>emitter-base voltage</td>
<td>open collector</td>
<td>-</td>
<td>-5</td>
<td>V</td>
</tr>
<tr>
<td>( I_C )</td>
<td>collector current (DC)</td>
<td></td>
<td>-</td>
<td>-1</td>
<td>A</td>
</tr>
<tr>
<td>( I_{CM} )</td>
<td>peak collector current</td>
<td>single pulse; ( t_p \leq 1) ms</td>
<td>-</td>
<td>-3</td>
<td>A</td>
</tr>
<tr>
<td>( I_B )</td>
<td>base current (DC)</td>
<td></td>
<td>-</td>
<td>-0.3</td>
<td>A</td>
</tr>
<tr>
<td>( P_{tot} )</td>
<td>total power dissipation</td>
<td>( T_{amb} \leq 25 ) °C</td>
<td>[1] -</td>
<td>0.55</td>
<td>W</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>[2] -</td>
<td>1.4</td>
<td>W</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>[3] -</td>
<td>2.0</td>
<td>W</td>
</tr>
<tr>
<td>( T_J )</td>
<td>junction temperature</td>
<td></td>
<td>-</td>
<td>150</td>
<td>°C</td>
</tr>
<tr>
<td>( T_{amb} )</td>
<td>ambient temperature</td>
<td></td>
<td>-65</td>
<td>+150</td>
<td>°C</td>
</tr>
<tr>
<td>( T_{stg} )</td>
<td>storage temperature</td>
<td></td>
<td>-65</td>
<td>+150</td>
<td>°C</td>
</tr>
</tbody>
</table>

[2] Device mounted on an FR4 PCB, mounting pad for collector 6cm².

Fig 1. Power derating curves

(1) Ceramic PCB, Al₂O₃, standard footprint
(2) FR4 PCB, mounting pad for collector 6cm²
(3) FR4 PCB, standard footprint
6. Thermal characteristics

Table 6. Thermal characteristics

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Parameter</th>
<th>Conditions</th>
<th>Min</th>
<th>Typ</th>
<th>Max</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>$R_{th(j-a)}$</td>
<td>thermal resistance from</td>
<td>in free air</td>
<td>[1]</td>
<td>-</td>
<td>227</td>
<td>K/W</td>
</tr>
<tr>
<td></td>
<td>junction to ambient</td>
<td></td>
<td>[2]</td>
<td>-</td>
<td>89</td>
<td>K/W</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>[3]</td>
<td>-</td>
<td>63</td>
<td>K/W</td>
</tr>
<tr>
<td>$R_{th(j-sp)}$</td>
<td>thermal resistance from</td>
<td></td>
<td>-</td>
<td>-</td>
<td>16</td>
<td>K/W</td>
</tr>
<tr>
<td></td>
<td>junction to solder point</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse time; typical values

FR4 PCB, standard footprint
**FR4 PCB, mounting pad for collector 6cm²**

**Fig 3. Transient thermal impedance from junction to ambient as a function of pulse time; typical values**

**Ceramic PCB, Al₂O₃, standard footprint**

**Fig 4. Transient thermal impedance from junction to ambient as a function of pulse time; typical values**
7. Characteristics

Table 7. Characteristics
*\(T_{\text{amb}} = 25 \, ^\circ\text{C}\) unless otherwise specified.

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Parameter</th>
<th>Conditions</th>
<th>Min</th>
<th>Typ</th>
<th>Max</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>(I_{\text{CBO}})</td>
<td>collector-base cut-off current</td>
<td>(V_{\text{CB}} = -80 , \text{V}; , I_{\text{E}} = 0 , \text{A}); (T_{\text{j}} = 150 , ^\circ\text{C})</td>
<td>-</td>
<td>-</td>
<td>-100</td>
<td>nA</td>
</tr>
<tr>
<td>(I_{\text{CES}})</td>
<td>collector-emitter cut-off current</td>
<td>(V_{\text{CE}} = -80 , \text{V}; , V_{\text{BE}} = 0 , \text{V})</td>
<td>-</td>
<td>-</td>
<td>-100</td>
<td>nA</td>
</tr>
<tr>
<td>(I_{\text{EBO}})</td>
<td>emitter-base cut-off current</td>
<td>(V_{\text{EB}} = -4 , \text{V}; , I_{\text{C}} = 0 , \text{A})</td>
<td>-</td>
<td>-</td>
<td>-100</td>
<td>nA</td>
</tr>
<tr>
<td>(h_{\text{FE}})</td>
<td>DC current gain</td>
<td>(V_{\text{CE}} = -5 , \text{V}; , I_{\text{C}} = -1 , \text{mA})</td>
<td>150</td>
<td>-</td>
<td>-</td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>(V_{\text{CE}} = -5 , \text{V}; , I_{\text{C}} = -250 , \text{mA})</td>
<td>150</td>
<td>-</td>
<td>-</td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>(V_{\text{CE}} = -5 , \text{V}; , I_{\text{C}} = -0.5 , \text{A})</td>
<td>150</td>
<td>-</td>
<td>450</td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>(V_{\text{CE}} = -5 , \text{V}; , I_{\text{C}} = -1 , \text{A})</td>
<td>125</td>
<td>-</td>
<td>-</td>
<td></td>
</tr>
<tr>
<td>(V_{\text{CEsat}})</td>
<td>collector-emitter saturation voltage</td>
<td>(I_{\text{C}} = -250 , \text{mA}; , I_{\text{B}} = -25 , \text{mA})</td>
<td>-</td>
<td>-</td>
<td>-120</td>
<td>mV</td>
</tr>
<tr>
<td></td>
<td></td>
<td>(I_{\text{C}} = -500 , \text{mA}; , I_{\text{B}} = -50 , \text{mA})</td>
<td>-</td>
<td>-</td>
<td>-180</td>
<td>mV</td>
</tr>
<tr>
<td></td>
<td></td>
<td>(I_{\text{C}} = -1 , \text{A}; , I_{\text{B}} = -100 , \text{mA})</td>
<td>-</td>
<td>-</td>
<td>-320</td>
<td>mV</td>
</tr>
<tr>
<td>(R_{\text{CEsat}})</td>
<td>collector-emitter saturation resistance</td>
<td>(I_{\text{C}} = -1 , \text{A}; , I_{\text{B}} = -100 , \text{mA})</td>
<td>-</td>
<td>170</td>
<td>320</td>
<td>m(\Omega)</td>
</tr>
<tr>
<td>(V_{\text{BEsat}})</td>
<td>base-emitter saturation voltage</td>
<td>(I_{\text{C}} = -1 , \text{A}; , I_{\text{B}} = -100 , \text{mA})</td>
<td>-</td>
<td>-</td>
<td>-1.1</td>
<td>V</td>
</tr>
<tr>
<td>(V_{\text{BEon}})</td>
<td>base-emitter turn-on voltage</td>
<td>(I_{\text{C}} = -1 , \text{A}; , V_{\text{CE}} = -5 , \text{V})</td>
<td>-</td>
<td>-</td>
<td>-1.0</td>
<td>V</td>
</tr>
<tr>
<td>(t_{\text{d}})</td>
<td>delay time</td>
<td>(V_{\text{CC}} = -10 , \text{V}; , I_{\text{C}} = -0.5 , \text{A})</td>
<td>20</td>
<td>-</td>
<td>ns</td>
<td></td>
</tr>
<tr>
<td>(t_{\text{r}})</td>
<td>rise time</td>
<td>(I_{\text{BON}} = 0.025 , \text{A}; , I_{\text{BOff}} = 0.025 , \text{A})</td>
<td>60</td>
<td>-</td>
<td>ns</td>
<td></td>
</tr>
<tr>
<td>(t_{\text{on}})</td>
<td>turn-on time</td>
<td>(V_{\text{CC}} = -10 , \text{V}; , I_{\text{C}} = -0.5 , \text{A})</td>
<td>80</td>
<td>-</td>
<td>ns</td>
<td></td>
</tr>
<tr>
<td>(t_{\text{s}})</td>
<td>storage time</td>
<td>(V_{\text{CC}} = -10 , \text{V}; , I_{\text{C}} = -0.5 , \text{A})</td>
<td>290</td>
<td>-</td>
<td>ns</td>
<td></td>
</tr>
<tr>
<td>(t_{\text{f}})</td>
<td>fall time</td>
<td>(V_{\text{CC}} = -10 , \text{V}; , I_{\text{C}} = -0.5 , \text{A})</td>
<td>120</td>
<td>-</td>
<td>ns</td>
<td></td>
</tr>
<tr>
<td>(t_{\text{off}})</td>
<td>turn-off time</td>
<td>(V_{\text{CC}} = -10 , \text{V}; , I_{\text{C}} = -0.5 , \text{A})</td>
<td>410</td>
<td>-</td>
<td>ns</td>
<td></td>
</tr>
<tr>
<td>(f_{\text{T}})</td>
<td>transition frequency</td>
<td>(I_{\text{C}} = -50 , \text{mA}; , V_{\text{CE}} = -10 , \text{V}; , f = 100 , \text{MHz})</td>
<td>100</td>
<td>-</td>
<td>-</td>
<td>MHz</td>
</tr>
<tr>
<td>(C_{\text{C}})</td>
<td>collector capacitance</td>
<td>(I_{\text{E}} = I_{\text{B}} = 0 , \text{A}; , V_{\text{CB}} = -10 , \text{V}; , f = 1 , \text{MHz})</td>
<td>-</td>
<td>-</td>
<td>17</td>
<td>pF</td>
</tr>
</tbody>
</table>

[1] Pulse test: \(t_{\text{p}} \leq 300 \, \mu\text{s}\); \(\delta \leq 0.02\).
**Fig 5.** DC current gain as a function of collector current; typical values

- $V_{CE} = -10\ V$
  - (1) $T_{amb} = 100\ ^\circ C$
  - (2) $T_{amb} = 25\ ^\circ C$
  - (3) $T_{amb} = -55\ ^\circ C$

**Fig 6.** Base-emitter voltage as a function of collector current; typical values

- $V_{CE} = -10\ V$
  - (1) $T_{amb} = -55\ ^\circ C$
  - (2) $T_{amb} = 25\ ^\circ C$
  - (3) $T_{amb} = 100\ ^\circ C$

**Fig 7.** Collector-emitter saturation voltage as a function of collector current; typical values

- $I_{C}/I_{B} = 10$
  - (1) $T_{amb} = 100\ ^\circ C$
  - (2) $T_{amb} = 25\ ^\circ C$
  - (3) $T_{amb} = -55\ ^\circ C$

**Fig 8.** Collector-emitter saturation voltage as a function of collector current; typical values

- $T_{amb} = 25\ ^\circ C$
  - (1) $I_{C}/I_{B} = 50$
  - (2) $I_{C}/I_{B} = 20$
**Product data sheet**

**NXP Semiconductors**

**PBSS9110X**

100 V, 1 A PNP low $V_{CE_{sat}}$ (BISS) transistor

---

**Fig 9. Base-emitter saturation voltage as a function of collector current; typical values**

- $I_C/I_B = 10$
- (1) $T_{amb} = -55 \degree C$
- (2) $T_{amb} = 25 \degree C$
- (3) $T_{amb} = 100 \degree C$

**Fig 10. Base-emitter saturation voltage as a function of collector current; typical values**

- $I_C/I_B = 20$
- $T_{amb} = 25 \degree C$

---

**Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values**

- $I_C/I_B = 10$
- (1) $T_{amb} = -55 \degree C$
- (2) $T_{amb} = 25 \degree C$
- (3) $T_{amb} = 100 \degree C$

**Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values**

- $T_{amb} = 25 \degree C$
- (1) $I_C/I_B = 50$
- (2) $I_C/I_B = 20$
Fig 13. Collector current as a function of collector-emitter voltage; typical values
8. Test information

**Fig 14. BISS transistor switching time definition**

- **Input pulse** (idealized waveform)
  - $-I_{B_{on}} (100\%)$
  - $-I_{B_{off}}$
- **Output pulse** (idealized waveform)
  - $-I_{C (100\%)}$
  - $-I_C$

- $t_d, t_{on}, t_r, t_f, t_{off}, t_o$

**Fig 15. Test circuit for switching times**

- $V_{CC} = -10\, V; I_C = -0.5\, A; I_{B_{on}} = -0.025\, A; I_{B_{off}} = 0.025\, A$
9. Package outline

![Package outline SOT89 (SC-62/TO-243)](image)

Fig 16. Package outline SOT89 (SC-62/TO-243)

10. Packing information

<table>
<thead>
<tr>
<th>Type number</th>
<th>Package</th>
<th>Description</th>
<th>Packing quantity</th>
</tr>
</thead>
<tbody>
<tr>
<td>PBSS9110X</td>
<td>SOT89</td>
<td>8 mm pitch, 12 mm tape and reel</td>
<td>1000 4000</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>-115 -135</td>
</tr>
</tbody>
</table>

[1] For further information and the availability of packing methods, see Section 15.
11. Soldering

SOT89 standard mounting conditions for reflow soldering
Dimensions in mm

Fig 17. Reflow soldering footprint SOT89 (SC-62/TO-243)

12. Mounting

Fig 18. FR4 PCB, standard footprint

Fig 19. FR4 PCB, mounting pad for collector 6cm²
## 13. Revision history

<table>
<thead>
<tr>
<th>Document ID</th>
<th>Release date</th>
<th>Data sheet status</th>
<th>Change notice</th>
<th>Supersedes</th>
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<td>PBSS9110X_2</td>
<td>20091122</td>
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<td>-</td>
<td>PBSS9110X_1</td>
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</tbody>
</table>

**Modifications:**
- This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.
- Figure 12 “Collector-emitter saturation resistance as a function of collector current; typical values”: updated
- Figure 13 “Collector current as a function of collector-emitter voltage; typical values”: updated

<table>
<thead>
<tr>
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<th>Release date</th>
<th>Data sheet status</th>
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<th>Supersedes</th>
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<td>20050502</td>
<td>Product data sheet</td>
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14. Legal information

14.1 Data sheet status

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<tbody>
<tr>
<td>Objective [short] data sheet</td>
<td>Development</td>
<td>This document contains data from the objective specification for product development.</td>
</tr>
<tr>
<td>Preliminary [short] data sheet</td>
<td>Qualification</td>
<td>This document contains data from the preliminary specification.</td>
</tr>
<tr>
<td>Product [short] data sheet</td>
<td>Production</td>
<td>This document contains the product specification.</td>
</tr>
</tbody>
</table>

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term ‘short data sheet’ is explained in section “Definitions”.
[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at URL http://www.nxp.com.

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16. Contents

<table>
<thead>
<tr>
<th>Section</th>
<th>Page</th>
</tr>
</thead>
<tbody>
<tr>
<td>1 Product profile</td>
<td>1</td>
</tr>
<tr>
<td>1.1 General description</td>
<td>1</td>
</tr>
<tr>
<td>1.2 Features</td>
<td>1</td>
</tr>
<tr>
<td>1.3 Applications</td>
<td>1</td>
</tr>
<tr>
<td>1.4 Quick reference data</td>
<td>1</td>
</tr>
<tr>
<td>2 Pinning information</td>
<td>2</td>
</tr>
<tr>
<td>3 Ordering information</td>
<td>2</td>
</tr>
<tr>
<td>4 Marking</td>
<td>2</td>
</tr>
<tr>
<td>5 Limiting values</td>
<td>3</td>
</tr>
<tr>
<td>6 Thermal characteristics</td>
<td>4</td>
</tr>
<tr>
<td>7 Characteristics</td>
<td>6</td>
</tr>
<tr>
<td>8 Test information</td>
<td>10</td>
</tr>
<tr>
<td>9 Package outline</td>
<td>11</td>
</tr>
<tr>
<td>10 Packing information</td>
<td>11</td>
</tr>
<tr>
<td>11 Soldering</td>
<td>12</td>
</tr>
<tr>
<td>12 Mounting</td>
<td>12</td>
</tr>
<tr>
<td>13 Revision history</td>
<td>13</td>
</tr>
<tr>
<td>14 Legal information</td>
<td>14</td>
</tr>
<tr>
<td>14.1 Data sheet status</td>
<td>14</td>
</tr>
<tr>
<td>14.2 Definitions</td>
<td>14</td>
</tr>
<tr>
<td>14.3 Disclaimers</td>
<td>14</td>
</tr>
<tr>
<td>14.4 Trademarks</td>
<td>14</td>
</tr>
<tr>
<td>15 Contact information</td>
<td>14</td>
</tr>
<tr>
<td>16 Contents</td>
<td>15</td>
</tr>
</tbody>
</table>